

WSP8205-VB Datasheet Dual N-Channel 25-V (D-S) MOSFET

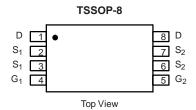
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
25	0.022 at V _{GS} = 4.5 V	6.6		
	0.032 at V _{GS} = 2.5 V	5.5		

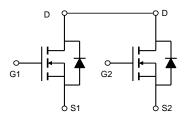
FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETs



RoHS*





ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	25		V
Gate-Source Voltage		V _{GS}	± 12		V
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	- I _D	6.6	5.2	
	T _A = 70 °C		5.5	3.5	•
Pulsed Drain Current		I _{DM}	30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0	
M ·	T _A = 25 °C	- P _D	1.5	1.0	W
Maximum Power Dissipation ^a	T _A = 70 °C		0.96	0.64	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Manifesture Investigate As Aughtentia	t ≤ 10 s	R _{thJA}	72	83	
Maximum Junction-to-Ambient ^a	Steady State	™thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	55	70	

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



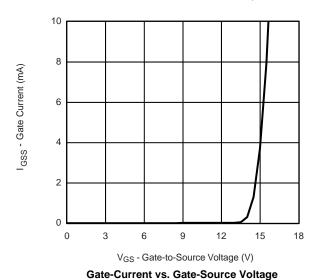
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Mi		Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.5		1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$			1		
	I _{DSS}	V_{DS} = 25 V, V_{GS} = 0 V, T_{J} = 70 °C			25	μA	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^b	D	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.022		Ω	
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.032			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 10 V, I _D = 6.5 A		30		S	
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Q_g			12	18		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q_{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495	ne	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_G = 6 \Omega$		860	1300	ns	
Fall Time	t _f			510	765		

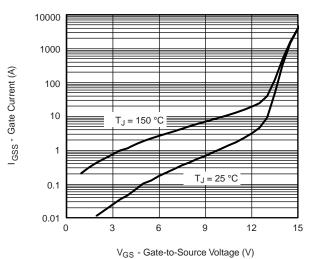
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

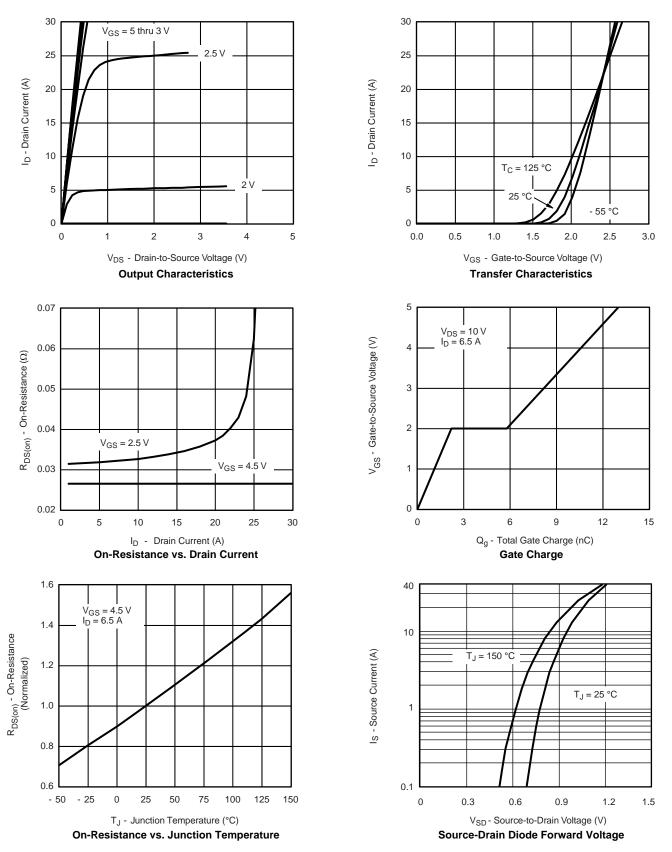




Gate Current vs. Gate-Source Voltage

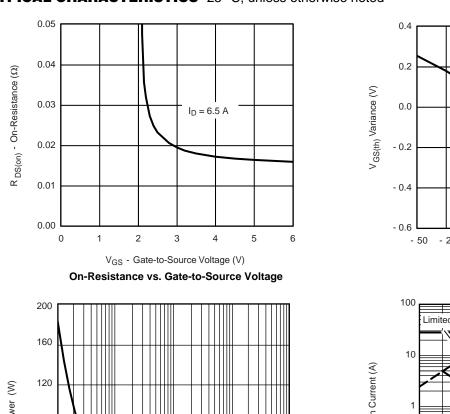


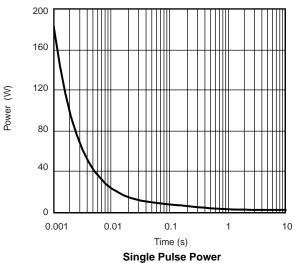
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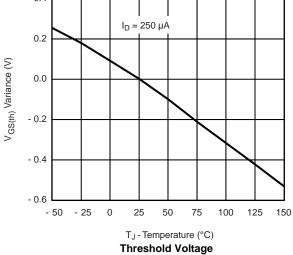


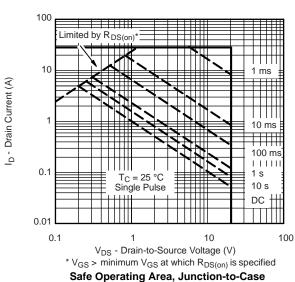


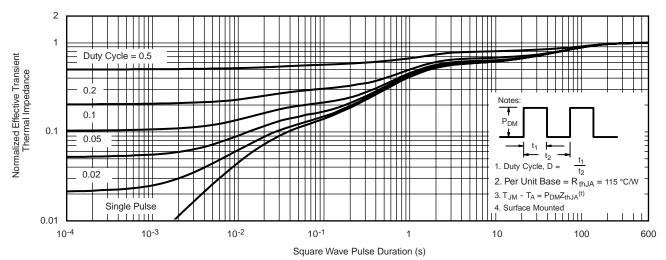
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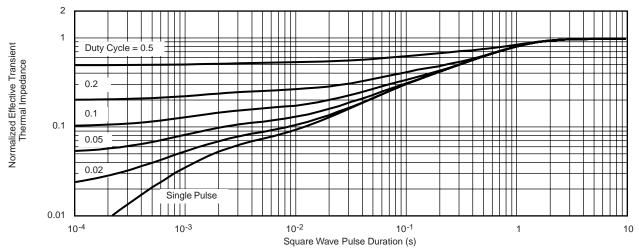




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

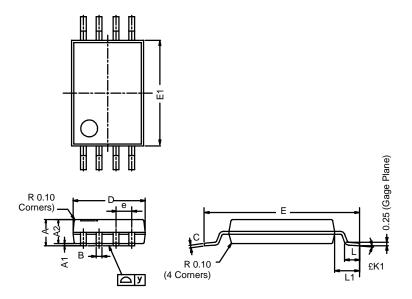


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP: 8-LEAD

JEDEC Part Number: MO-153

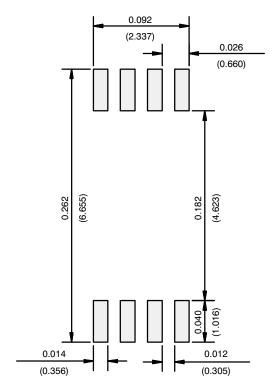


	MILLIMETERS			
Dim	Min	Nom	Max	
Α	-	-	1.20	
A ₁	0.05	0.10	0.15	
A ₂	0.80	1.00	1.05	
В	0.19	0.28	0.30	
С	-	0.127	-	
D	2.90	3.00	3.10	
Е	6.20	6.40	6.60	
E ₁	4.30	4.40	4.50	
е	-	0.65	-	
L	0.45	0.60	0.75	
L ₁	0.90	1.00	1.10	
Y	-	-	0.10	
£ K1	0°	3°	6°	
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844				



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RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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